

Dominik Metzler

List of Publications by Year in descending order

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14
papers

514
citations

933447

10
h-index

1125743

13
g-index

14
all docs

14
docs citations

14
times ranked

311
citing authors

#	ARTICLE	IF	CITATIONS
1	Significance of plasma-photoresist interactions for atomic layer etching processes with extreme ultraviolet photoresist. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	4
2	Selective atomic layer etching of HfO ₂ over silicon by precursor and substrate-dependent selective deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	16
3	Achieving ultrahigh etching selectivity of SiO ₂ over Si ₃ N ₄ and Si in atomic layer etching by exploiting chemistry of complex hydrofluorocarbon precursors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	40
4	Characterizing fluorocarbon assisted atomic layer etching of Si using cyclic Ar/C ₄ F ₈ and Ar/CHF ₃ plasma. Journal of Chemical Physics, 2017, 146, 052801.	3.0	35
5	Investigation of thin oxide layer removal from Si substrates using an SiO ₂ atomic layer etching approach: the importance of the reactivity of the substrate. Journal Physics D: Applied Physics, 2017, 50, 254006.	2.8	24
6	He plasma pretreatment of organic masking materials for performance improvement during pattern transfer by plasma etching. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, 041604.	1.2	5
7	Application of cyclic fluorocarbon/argon discharges to device patterning. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	17
8	Fluorocarbon based atomic layer etching of Si ₃ N ₄ and etching selectivity of SiO ₂ over Si ₃ N ₄ . Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	75
9	Effect of the chamber wall on fluorocarbon-assisted atomic layer etching of SiO ₂ using cyclic Ar/C ₄ F ₈ plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 040603.	2.1	24
10	Fluorocarbon assisted atomic layer etching of SiO ₂ and Si using cyclic Ar/C ₄ F ₈ and Ar/CHF ₃ plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	74
11	Formation of nanometer-thick delaminated amorphous carbon layer by two-step plasma processing of methacrylate-based polymer. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	1.2	8
12	Controlling Asymmetric Photoresist Feature Dimensions during Plasma-Assisted Shrink. Plasma Processes and Polymers, 2014, 11, 714-720.	3.0	0
13	Fluorocarbon assisted atomic layer etching of SiO ₂ using cyclic Ar/C ₄ F ₈ plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	161
14	Feasibility of atomic layer etching of polymer material based on sequential O ₂ exposure and Ar low-pressure plasma-etching. Applied Physics Letters, 2013, 102, .	3.3	31